# **74AUP1G00**

# Low-power 2-input NAND gate Rev. 6 — 27 June 2012

**Product data sheet** 

#### **General description** 1.

The 74AUP1G00 provides the single 2-input NAND function.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V<sub>CC</sub> range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V<sub>CC</sub> range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I<sub>OFF</sub>.

The I<sub>OFF</sub> circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

#### 2. **Features and benefits**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - ◆ JESD8-12 (0.8 V to 1.3 V)
  - ◆ JESD8-11 (0.9 V to 1.65 V)
  - ◆ JESD8-7 (1.2 V to 1.95 V)
  - ◆ JESD8-5 (1.8 V to 2.7 V)
  - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; I<sub>CC</sub> = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



## 3. Ordering information

Table 1. Ordering information

Type number	Package							
	Temperature range	Name	Description	Version				
74AUP1G00GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1				
74AUP1G00GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1.45 $\times$ 0.5 mm	SOT886				
74AUP1G00GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891				
74AUP1G00GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115				
74AUP1G00GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202				
74AUP1G00GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226				

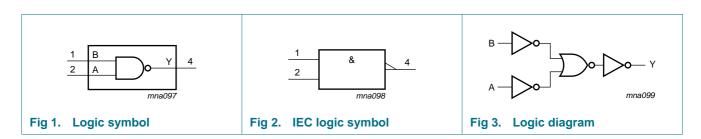
### 4. Marking

Table 2. Marking

Type number	Marking code <sup>[1]</sup>
74AUP1G00GW	pA
74AUP1G00GM	pA
74AUP1G00GF	pA
74AUP1G00GN	pA
74AUP1G00GS	pA
74AUP1G00GX	pA

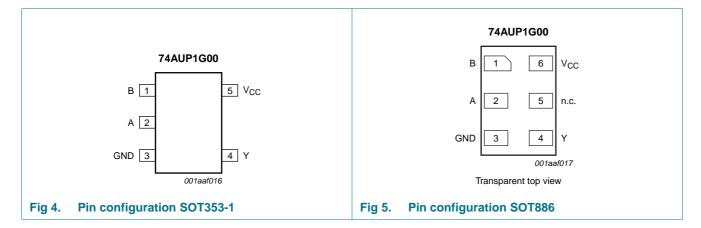
<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

### 5. Functional diagram



### 6. Pinning information

#### 6.1 Pinning





### 6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	TSSOP5 and X2SON5	XSON6	
В	1	1	data input
Α	2	2	data input
GND	3	3	ground (0 V)
Υ	4	4	data output
n.c.	-	5	not connected
V <sub>CC</sub>	5	6	supply voltage

### 7. Functional description

Table 4. Function table[1]

Input		Output
Α	В	Υ
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level.

### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					=
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
V <sub>I</sub>	input voltage		[ <u>1</u> ] -0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode	[ <u>1</u> ] -0.5	$V_{CC} + 0.5$	V
		Power-down mode	[ <u>1</u> ] -0.5	+4.6	V
I <sub>O</sub>	output current	$V_O = 0 V to V_{CC}$	-	±20	mA
I <sub>CC</sub>	supply current		-	+50	mA
$I_{GND}$	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C}$ to +125 $^{\circ}\text{C}$	[2] _	250	mW

<sup>[1]</sup> The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

### 9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		0.8	3.6	V
V <sub>I</sub>	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	$V_{CC}$	V
		Power-down mode; V <sub>CC</sub> = 0 V	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	0	200	ns/V

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<sup>[2]</sup> For TSSOP5 packages: above 87.5 °C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K.
For XSON6 and X2SON5 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

### 10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

V <sub>IL</sub>	HIGH-level input voltage  LOW-level input voltage	$V_{CC} = 0.8 \text{ V}$ $V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 0.8 \text{ V}$ $V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.70 × V <sub>CC</sub> 0.65 × V <sub>CC</sub> 1.6 2.0 -		- - - 0.30 × V <sub>CC</sub>	V V V V
$V_IL$	LOW-level input voltage	$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 0.8 \text{ V}$ $V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.65 × V <sub>CC</sub> 1.6 2.0 -			V V V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 0.8 \text{ V}$ $V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6 2.0 -	- - - -		V V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 0.8 \text{ V}$ $V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.0	- - -		V
		$V_{CC} = 0.8 \text{ V}$ $V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-			
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-		V
	HIGH-level output voltage	V <sub>CC</sub> = 2.3 V to 2.7 V		-		
	HIGH-level output voltage		-		$0.35 \times V_{CC}$	V
.,	HIGH-level output voltage	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	0.7	V
. ,	HIGH-level output voltage		-	-	0.9	V
$V_{OH}$		$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O} = -20 \mu A$ ; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_O = 1.9 \text{ mA}$ ; $V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
l	input leakage current	$V_I$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	±0.1	μΑ
$I_{OFF}$	power-off leakage current	$V_I$ or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
lcc	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
Δl <sub>CC</sub>	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	[1] -	-	40	μΑ
Cı	input capacitance	$V_{CC} = 0 \text{ V to } 3.6 \text{ V; } V_{I} = \text{GND or } V_{CC}$	-	0.8	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.7	-	pF

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 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = -	40 °C to +85 °C					
$V_{IH}$	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
$V_{IL}$	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	$0.30 \times V_{CC}$	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O = -20 \mu A$ ; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC}$	V
		$I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.33	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I	input leakage current	$V_I$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	±0.5	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_I$ or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μΑ
I <sub>CC</sub>	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μΑ
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	[1] -	-	50	μΑ

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = -	40 °C to +125 °C					
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	$0.75 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC}$ = 3.0 V to 3.6 V	2.0	-	-	V
$V_{IL}$	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	$0.25 \times V_{CC}$	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O} = -20 \mu A$ ; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	V <sub>CC</sub> – 0.11	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_{O}$ = 1.9 mA; $V_{CC}$ = 1.65 V	-	-	0.39	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.36	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
l <sub>l</sub>	input leakage current	$V_I$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	±0.75	μΑ
OFF	power-off leakage current	$V_I$ or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I <sub>CC</sub>	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
Δl <sub>CC</sub>	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	[1] -	-	75	μΑ

<sup>[1]</sup> One input at  $V_{CC}$  – 0.6 V, other input at  $V_{CC}$  or GND.

## 11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9

Symbol	Parameter	Conditions		Min	Typ 🗓	Max	Unit
T <sub>amb</sub> = 25	°C; C <sub>L</sub> = 5 pF						
t <sub>pd</sub>	propagation delay	A, B to Y; see Figure 8	[2]				
		$V_{CC} = 0.8 \text{ V}$		-	17.5	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.5	5.3	11.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.0	3.8	6.8	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.6	3.1	5.3	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.3	2.5	4.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.0	2.2	3.6	ns
T <sub>amb</sub> = 25	°C; C <sub>L</sub> = 10 pF						
t <sub>pd</sub>	propagation delay	A, B to Y; see Figure 8	[2]				
		$V_{CC} = 0.8 \text{ V}$		-	21.0	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.4	6.1	13.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.4	4.4	7.9	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.0	3.7	6.2	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.4	3.0	4.7	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.3	2.8	4.3	ns
T <sub>amb</sub> = 25	°C; C <sub>L</sub> = 15 pF						
t <sub>pd</sub>	propagation delay	A, B to Y; see Figure 8	[2]				
		$V_{CC} = 0.8 \text{ V}$		-	24.5	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.4	6.9	14.8	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.8	5.0	8.9	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.0	4.1	7.0	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.7	3.5	5.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.6	3.2	4.9	ns
T <sub>amb</sub> = 25	°C; C <sub>L</sub> = 30 pF						
t <sub>pd</sub>	propagation delay	A, B to Y; see Figure 8	[2]				
		$V_{CC} = 0.8 \text{ V}$		-	34.8	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.6	9.2	20.1	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		3.0	6.5	11.8	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.6	5.4	9.3	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.4	4.6	7.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.3	4.3	6.5	ns

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9

Symbol	Parameter	Conditions		Min	Typ 🗓	Max	Unit	
$T_{amb} = 25$	T <sub>amb</sub> = 25 °C							
$C_{PD}$	power dissipation capacitance	$f = 1 \text{ MHz}$ ; $V_I = \text{GND to } V_{CC}$	[3]					
		$V_{CC} = 0.8 \text{ V}$		-	2.6	-	pF	
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		-	2.8	-	pF	
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	2.9	-	pF	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	3.1	-	pF	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	3.6	-	pF	
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	4.2	-	pF	

<sup>[1]</sup> All typical values are measured at nominal  $V_{CC}$ .

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9

Symbol	Parameter	arameter Conditions		–40 °C t	:o +85 °C	-40 °C to	+125 °C	Unit
				Min	Max	Min	Max	
$C_L = 5 pF$								
t <sub>pd</sub>	propagation delay	A, B to Y; see Figure 8	<u>[1]</u>					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.1	12.2	2.1	13.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		1.8	7.8	1.8	8.6	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.4	6.2	1.4	6.9	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.1	4.7	1.1	5.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.0	4.2	1.0	4.7	ns
C <sub>L</sub> = 10 pF								
t <sub>pd</sub>	propagation delay	A, B to Y; see Figure 8	<u>[1]</u>					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.2	14.4	2.2	15.9	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.2	9.2	2.2	10.2	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.9	7.3	1.9	8.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.3	5.6	1.3	6.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.2	4.9	1.2	5.4	ns

<sup>[2]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

<sup>[3]</sup>  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 Table 9.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9

Symbol	Parameter	Conditions		–40 °C t	o +85 °C	–40 °C to	+125 °C	Unit
				Min	Max	Min	Max	
C <sub>L</sub> = 15 pl			'				'	1
t <sub>pd</sub>	propagation delay	A, B to Y; see Figure 8	[1]					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.1	16.5	3.1	18.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.5	10.5	2.5	11.6	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.0	8.3	2.0	9.2	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.5	6.4	1.5	7.1	ns
$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$			1.4	5.7	1.4	6.3	ns	
C <sub>L</sub> = 30 pl	•							
t <sub>pd</sub>	propagation delay	A, B to Y; see Figure 8	[1]					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.1	22.6	4.1	24.9	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.9	14.0	2.9	15.4	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.3	11.1	2.3	12.3	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.1	8.5	2.1	9.4	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.1	7.6	2.1	8.4	ns

<sup>[1]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

### 12. Waveforms

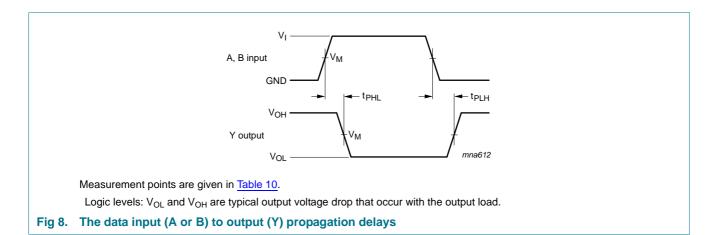
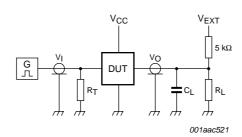


Table 10. Measurement points

Supply voltage	Output	Input		
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>I</sub>	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V <sub>CC</sub>	≤ 3.0 ns

#### Low-power 2-input NAND gate



Test data is given in Table 11.

Definitions for test circuit:

 $R_L$  = Load resistance.

 $C_L$  = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to the output impedance  $Z_0$  of the pulse generator.

 $V_{EXT}$  = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 11. Test data

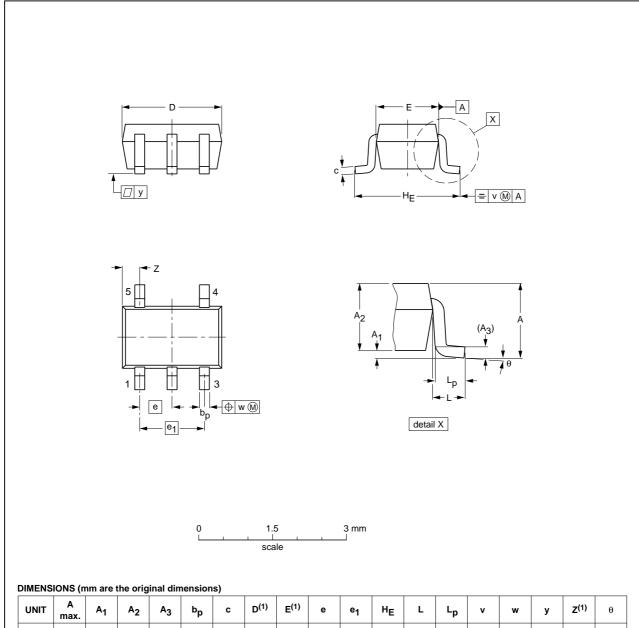
Supply voltage	Load		V <sub>EXT</sub>				
V <sub>CC</sub>	CL	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>		
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	$2\times V_{CC}$		

[1] For measuring enable and disable times  $R_L$  = 5  $k\Omega$ , for measuring propagation delays, setup and hold times and pulse width  $R_L$  = 1  $M\Omega$ .

### 13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	e <sub>1</sub>	HE	L	Lp	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

	REFER	ENCES	EUROPEAN	ISSUE DATE	
IEC	C JEDEC JEITA		PROJECTION	ISSUE DATE	
	MO-203	SC-88A		<del>-00-09-01</del> 03-02-19	
	IEC	IEC JEDEC	IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION	

Fig 10. Package outline SOT353-1 (TSSOP5)

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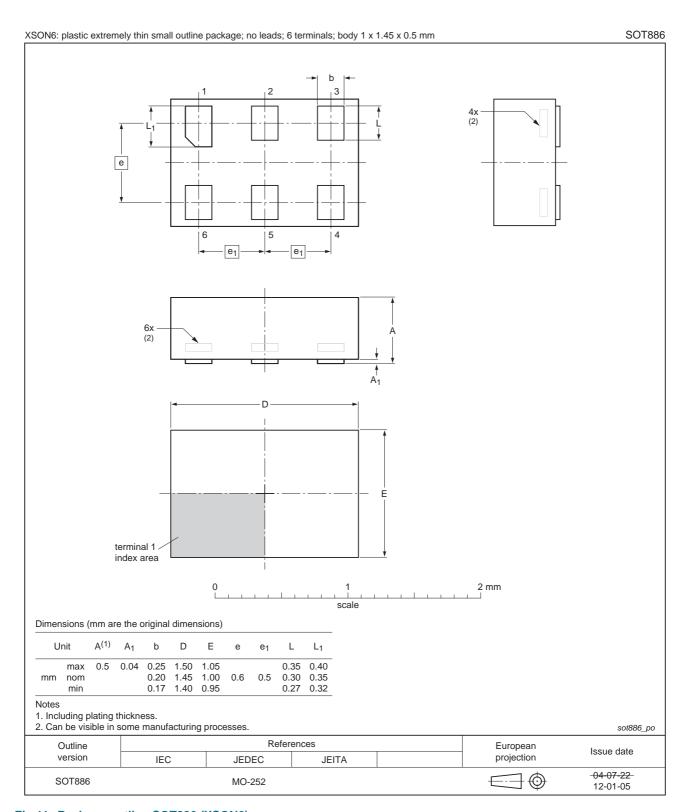


Fig 11. Package outline SOT886 (XSON6)

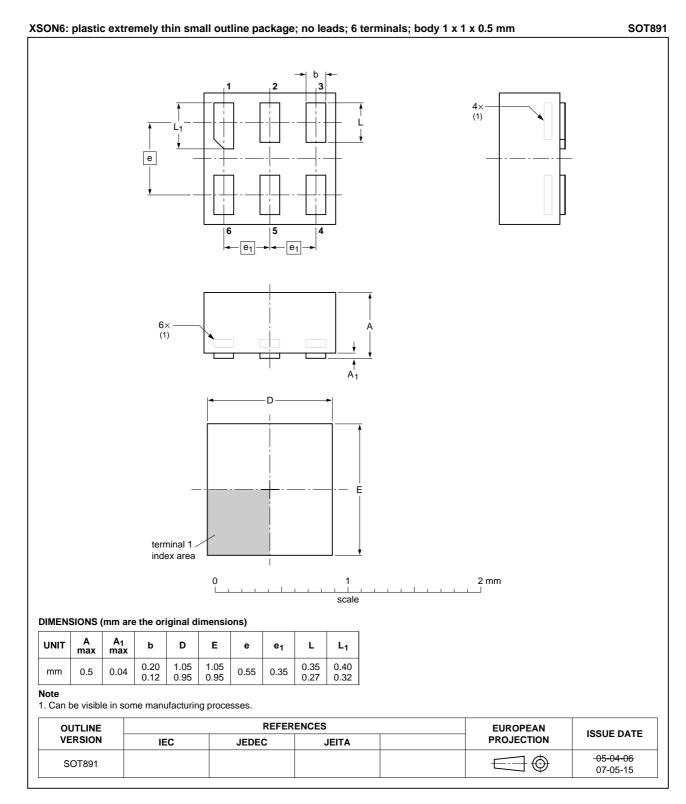


Fig 12. Package outline SOT891 (XSON6)

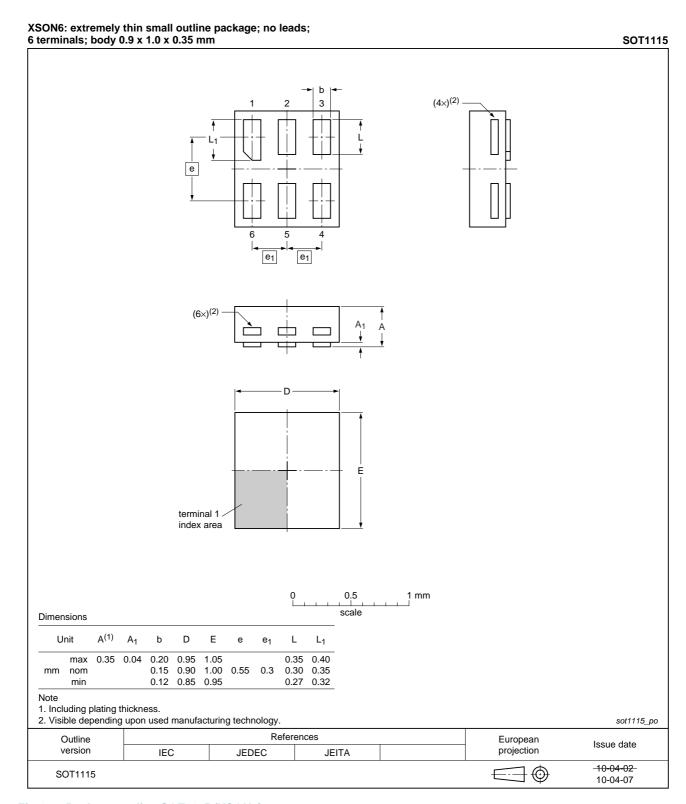


Fig 13. Package outline SOT1115 (XSON6)

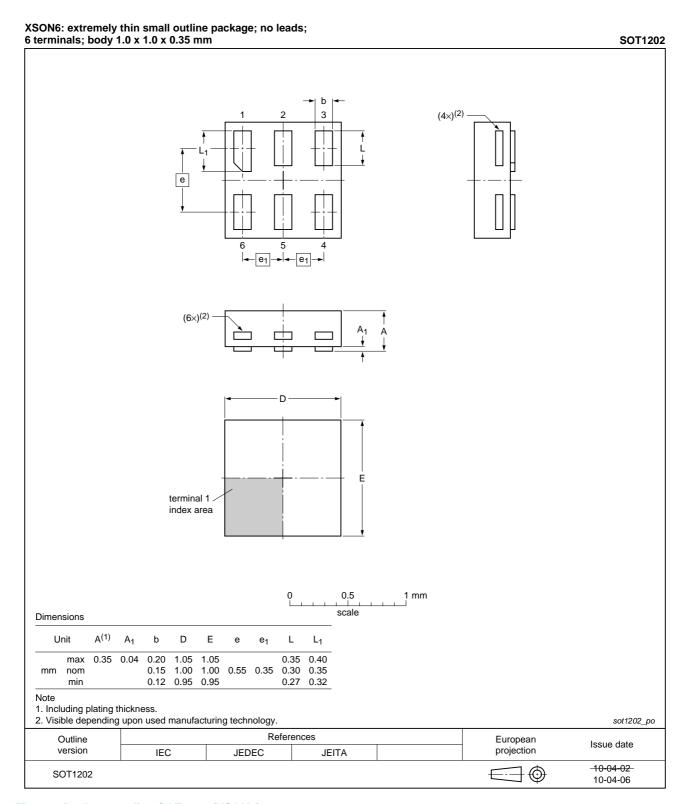


Fig 14. Package outline SOT1202 (XSON6)

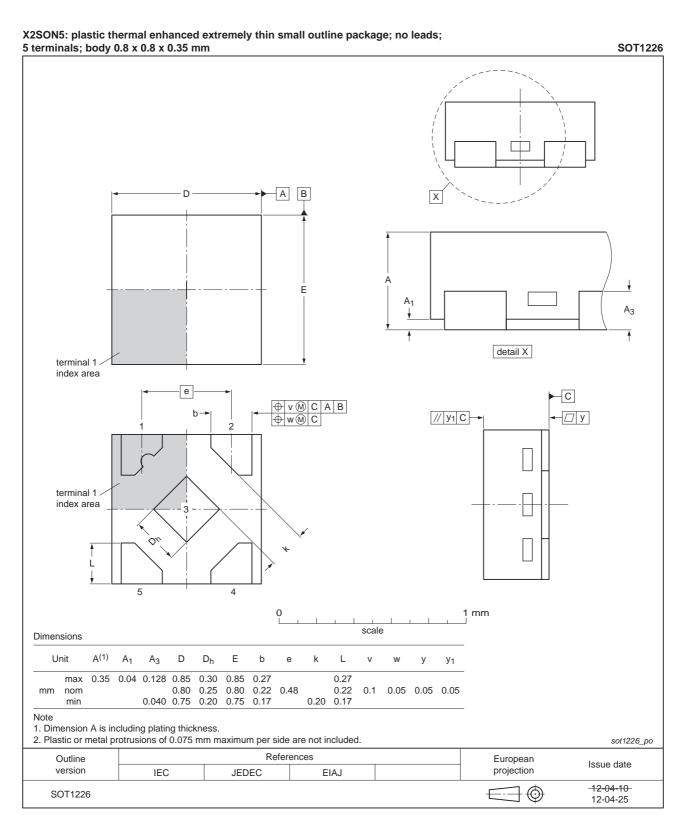


Fig 15. Package outline SOT1226 (X2SON5)

Low-power 2-input NAND gate

### 14. Abbreviations

#### **Table 12: Abbreviations**

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

# 15. Revision history

#### Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G00 v.6	20120627	Product data sheet	-	74AUP1G00 v.5
Modifications:	<ul> <li>Added type r</li> </ul>	number 74AUP1G00GX (SO	Г1226).	
74AUP1G00 v.5	20120316	Product data sheet	-	74AUP1G00 v.4
Modifications:	<ul> <li>Package out</li> </ul>	line drawing of SOT886 (Figu	<u>ire 11</u> ) modified.	
74AUP1G00 v.4	20111115	Product data sheet	-	74AUP1G00 v.3
Modifications:	<ul> <li>Legal pages</li> </ul>	updated.		
74AUP1G00 v.3	20101007	Product data sheet	-	74AUP1G00 v.2
74AUP1G00 v.2	20060629	Product data sheet	-	74AUP1G00 v.1
74AUP1G00 v.1	20050711	Product data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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#### Low-power 2-input NAND gate

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### Low-power 2-input NAND gate

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